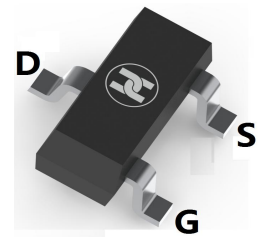
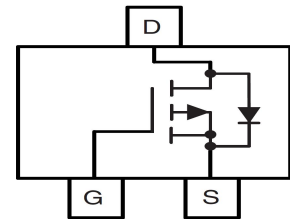


P-Channel Power MOSFET
FEATURES

- $V_{DS} = -20V, R_{DS(ON)} \leq 42m\Omega @ V_{GS} = -4.5V, I_D = -5A$
- Ultra Low On-Resistance
- P-Channel MOSFET
- Fast Switching


SOT-23

MECHANICAL DATA

- Case: SOT-23
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Weight: 0.008 grams (approximate)
- Marking: 1E

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-5	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-3.7	
I_{DM}	Pulsed Drain Current ①	-22	
$P_D @ T_A = 25^\circ C$	Power Dissipation	1.3	W
$P_D @ T_A = 70^\circ C$	Power Dissipation	0.8	
	Linear Derating Factor	0.01	W/°C
E_{AS}	Single Pulse Avalanche Energy④	11	mJ
V_{GS}	Gate-to-Source Voltage	± 12	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

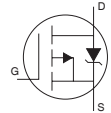
	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	75	100	°C/W

Electrical Characteristics @ $T_J = 25^\circ C$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.009	—	V/°C	Reference to 25°C, $I_D = -1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance		32	42	mΩ	$V_{GS} = -4.5V, I_D = -5A$
			42	60		$V_{GS} = -2.5V, I_D = -3A$
$V_{GS(th)}$	Gate Threshold Voltage	-0.4	-0.65	-1.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	6.0	—	—	S	$V_{DS} = -10V, I_D = -3.7A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -20V, V_{GS} = 0V, T_J = 70^\circ C$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -12V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 12V$
Q_g	Total Gate Charge	—	8.0	12	nC	$I_D = -3.7A$
Q_{gs}	Gate-to-Source Charge	—	1.2	1.8		$V_{DS} = -10V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	2.8	4.2		$V_{GS} = -5.0V$ ②
$t_{d(on)}$	Turn-On Delay Time	—	350	—	ns	$V_{DD} = -10V$
t_r	Rise Time	—	48	—		$I_D = -3.7A$
$t_{d(off)}$	Turn-Off Delay Time	—	588	—		$R_G = 89\Omega$
t_f	Fall Time	—	381	—		$R_D = 2.7\Omega$
C_{iss}	Input Capacitance	—	633	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	145	—		$V_{DS} = -10V$
C_{rss}	Reverse Transfer Capacitance	—	110	—		$f = 1.0MHz$

P-Channel Power MOSFET

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-22		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}$, $I_S = -1.0\text{A}$, $V_{GS} = 0\text{V}$ ②
t_{rr}	Reverse Recovery Time	—	29	43	ns	$T_J = 25^\circ\text{C}$, $I_F = -1.0\text{A}$
Q_{rr}	Reverse RecoveryCharge	—	11	17	nC	$di/dt = -100\text{A}/\mu\text{s}$ ②

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ③ Surface mounted on 1" square single layer 1oz. copper FR4 board, steady state.
- ④ Starting $T_J = 25^\circ\text{C}$, $L = 1.65\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = -3.7\text{A}$.

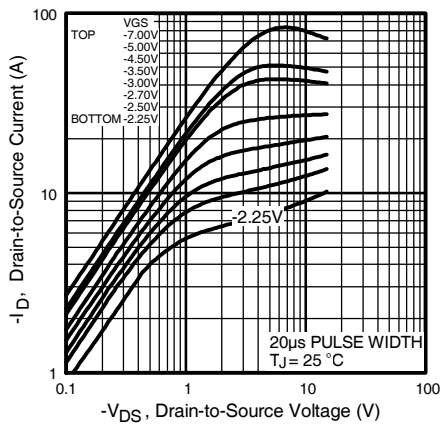


Fig 1. Typical Output Characteristics

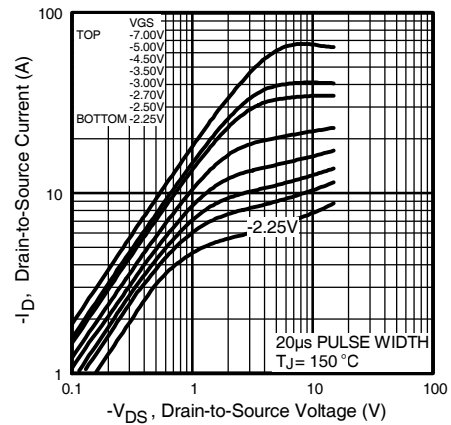


Fig 2. Typical Output Characteristics

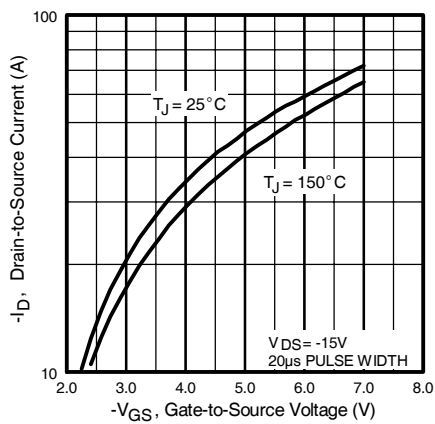


Fig 3. Typical Transfer Characteristics

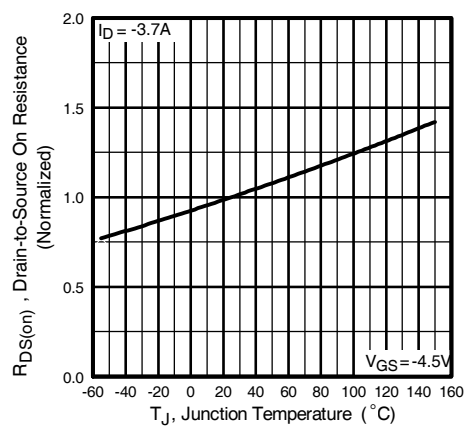


Fig 4. Normalized On-Resistance Vs. Temperature

P-Channel Power MOSFET

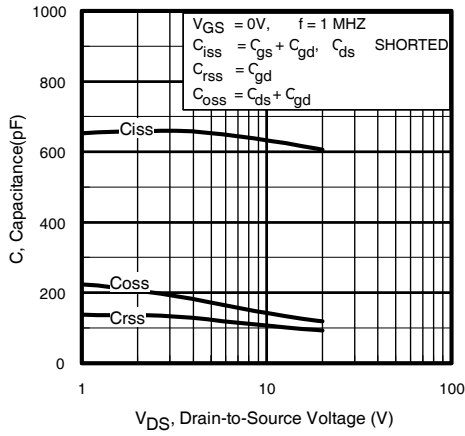


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

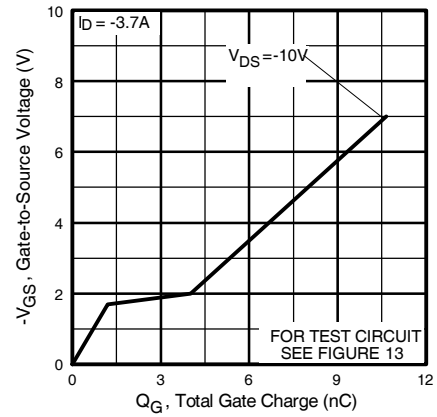


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

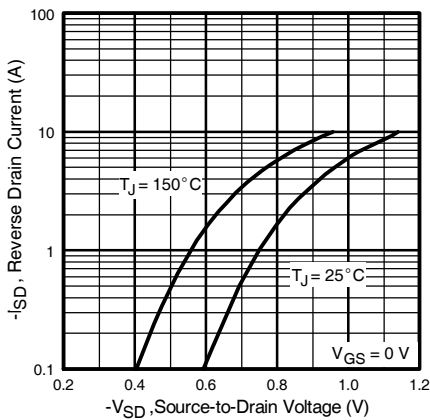


Fig 7. Typical Source-Drain Diode Forward Voltage

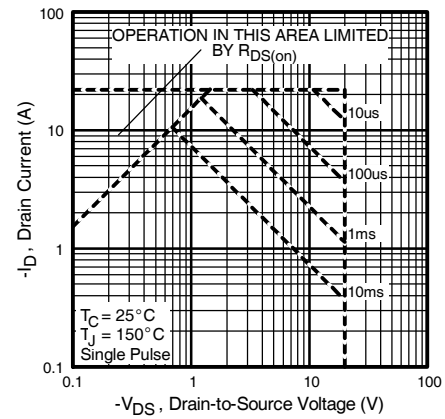


Fig 8. Maximum Safe Operating Area

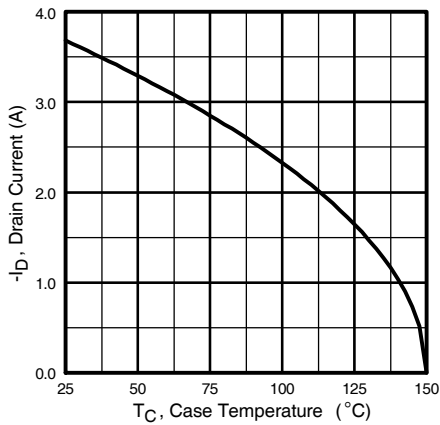


Fig 9. Maximum Drain Current Vs. Case Temperature

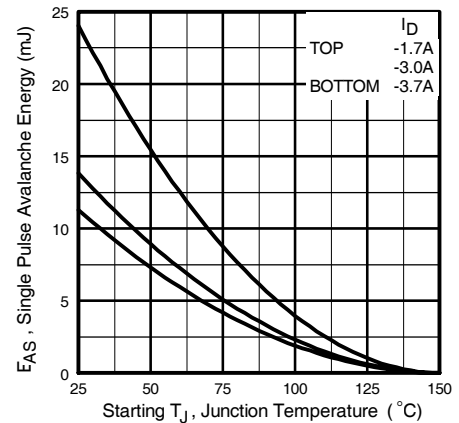


Fig 10. Maximum Avalanche Energy Vs. Drain Current

P-Channel Power MOSFET

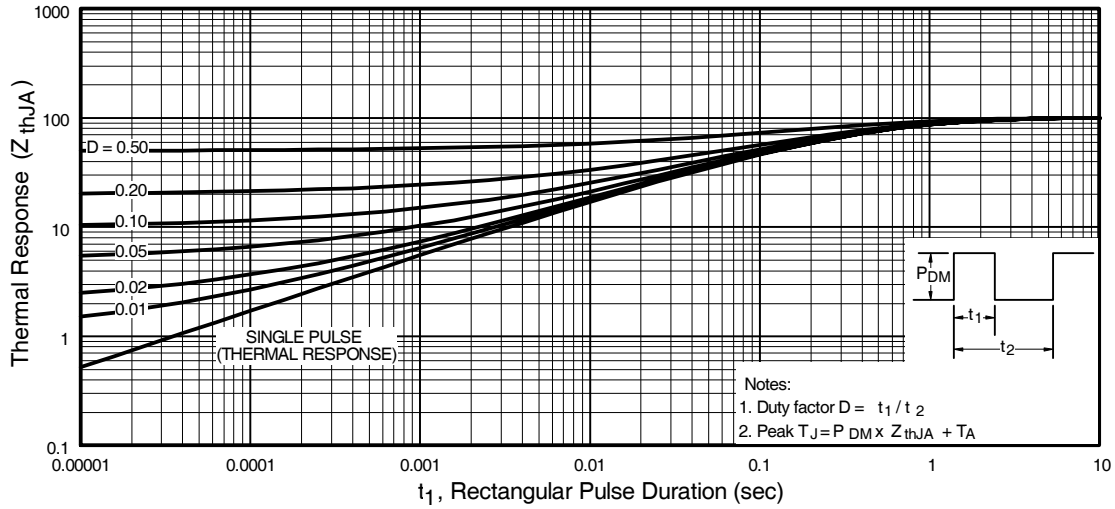


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

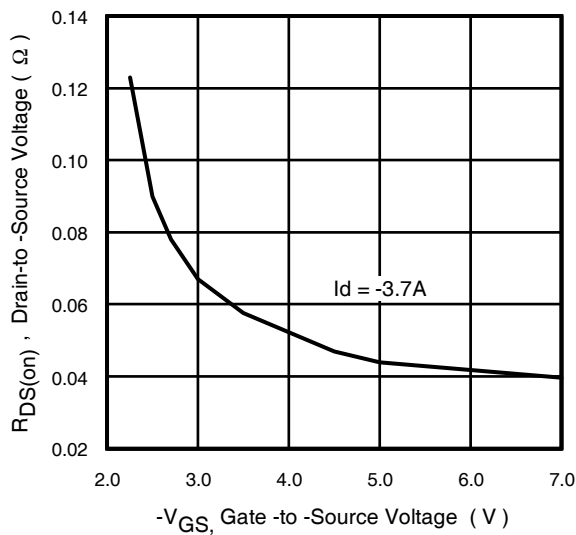


Fig 12. Typical On-Resistance Vs. Gate Voltage

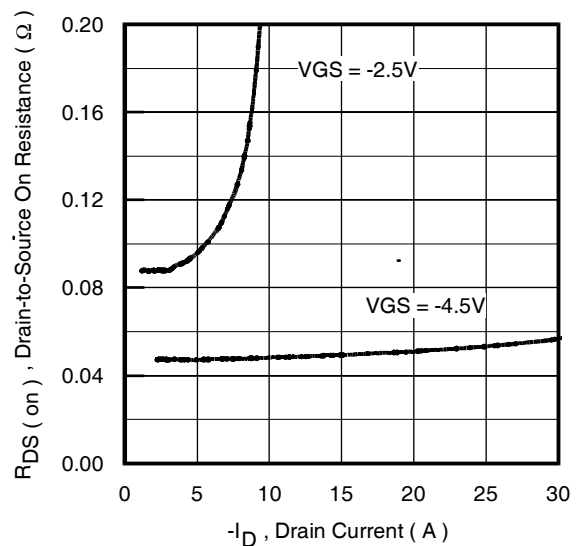
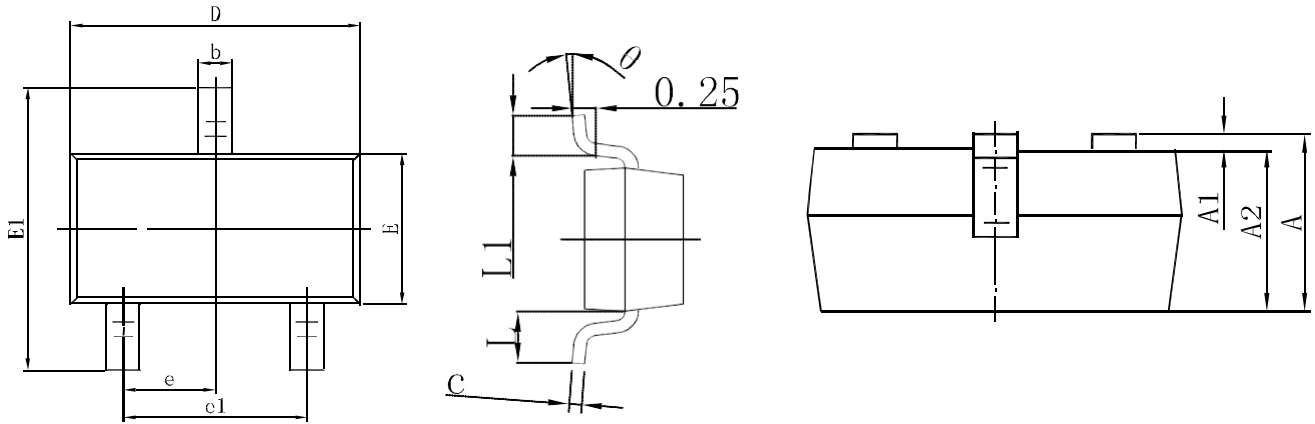
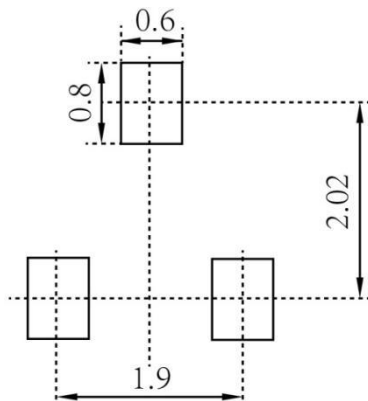


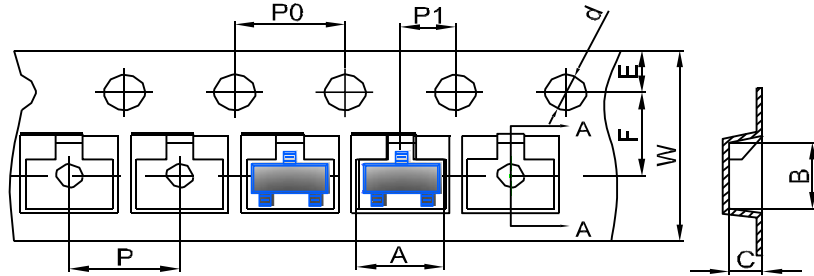
Fig 13. Typical On-Resistance Vs. Drain Current

P-Channel Power MOSFET
SOT-23 Package Outline Dimensions


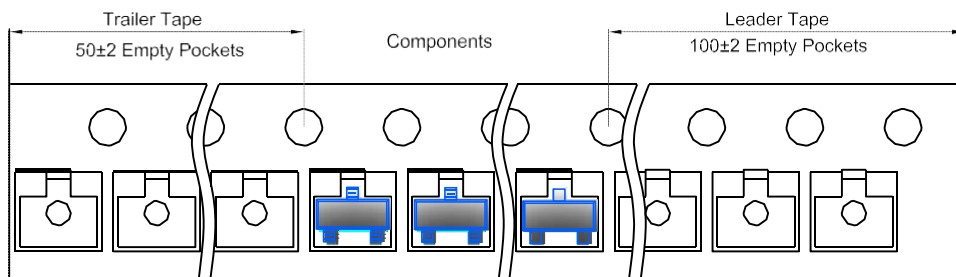
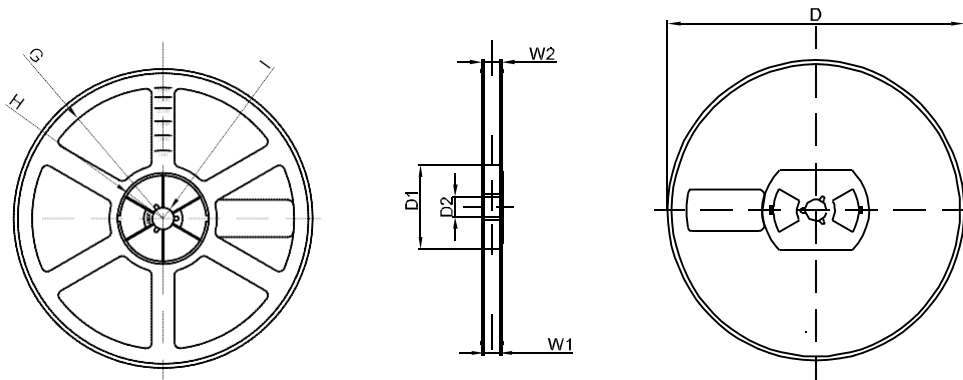
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout

Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

P-Channel Power MOSFET
SOT-23 Tape and Reel
SOT-23 Embossed Carrier Tape


DIMENSIONS ARE IN MILLIMETER										
TYPE	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

SOT-23 Tape Leader and Trailer

SOT-23 Reel


DIMENSIONS ARE IN MILLIMETER								
REEL OPTION	D	D1	D2	G	H	I	W1	W2
7" DIA	Ø178	54.40	13.00	R78	R25.60	R6.50	9.50	12.30
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1